

## High-Bandwidth, Low Voltage, Dual SPDT Analog Switches

### **DESCRIPTION**

The DG2519E is monolithic CMOS dual single-pole / double-throw (SPDT) analog switches. It is specifically designed for low-voltage, high bandwidth applications.

The DG2519E on-resistance, matching and flatness are guaranteed over the entire analog voltage range. Wide dynamic performance is achieved with typical at -61 dB for both cross-talk and off-isolation at 1 MHz.

Both SPDT's operate with independent control logic, conduct equally well in both directions and block signals up to the power supply level when off. Break-before-make is guaranteed.

With fast switching speeds, low on-resistance, high bandwidth, and low charge injection, the DG2519E are ideally suited for audio and video switching with high linearity.

Built on Vishay Siliconix's low voltage CMOS technology, the DG2519E contain an epitaxial layer which prevents latch-up

### **FEATURES**

- Single supply (1.8 V to 5.5 V)
- Low on-resistance  $R_{ON}$ : 2.5  $\Omega$



MSOP-10 and DFN-10 package

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



RoHS COMPLIAN

COMPLIANT HALOGEN

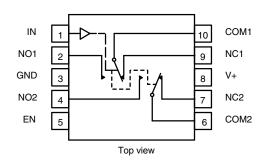
#### **BENEFITS**

- Reduced power consumption
- High accuracy
- Reduce board space
- · Low-voltage logic compatible
- · High bandwidth

### **APPLICATIONS**

- Cellular phones
- · Speaker headset switching
- · Audio and video signal routing
- PCMCIA cards
- · Low-voltage data acquisition
- ATE

### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



TRUTH TABLE							
LOGIC	EN	NC1 and NC2	NO1 and NO2				
0	1	ON	OFF				
1	1	OFF	ON				
0	0	OFF	OFF				
1	0	OFF	OFF				

ORDERING INFORMATION							
ORDERING INFORMATION							
TEMP. RANGE	TEMP. RANGE PACKAGE						
-40 °C to +85 °C	MSOP-10	DG2519EDQ-T1-GE3					
	DFN-10	DG2519EDN-T1-GE4					

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		LIMIT	UNIT				
Reference V+ to GND		-0.3 to +6	V				
IN, COM, NC, NO <sup>a</sup>		-0.3 to (V+ + 0.3)	V				
Continuous current (any terminal)		± 50	mA				
Peak current (pulsed at 1 ms, 10 % dut	cy cycle)	± 200	IIIA				
Storage temperature (D suffix)		-65 to +150	°C				
Power dissipation (packages) b	MSOP-10 °	320	mW				
Power dissipation (packages)	DFN-10 <sup>d</sup>	1191	IIIVV				
ESD / HBM EIA / JESD22-A114-A		7.5k	V				
ESD / CDM EIA / JESD22-C101-A		1.5k	V				
Latch up	JESD78	300	mA				

#### Notes

- a. Signals on NC, NO, COM, IN, or EN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 4 mW/°C above 70 °C
- d. Derate 14.9 mW/°C above 70 °C



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SPECIFICATIONS (V+	= 3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED $V+=3V,\pm10\%, V_{IN/ENL}=0.4V, V_{IN/ENH}=1.5V^{\circ}$		TEMP.	LIMITS -40 °C to +85 °C			UNIT
				1	MIN. c	TYP. b	MAX. c	
Analog Switch								
Analog signal range d	$V_{ANALOG}$				0	-	V+	V
		$V_{+} = 1.8 \text{ V}, V_{NC/NO} = 0.4 \text{ V} / V_{+}, I_{NO}$	- 2 mΔ	Room	-	7	11	
Drain-source on-resistance	R <sub>DS(on)</sub>	V+ = 1.0 V, VNC/NO = 0.4 V / V+, INC	;/NO = 0 111/A	Full	-	-	13	
Diani source on resistance	1 (DS(on)	$V_{+} = 2.7 \text{ V}, V_{COM} = 0.8 \text{ V} / 1.8 \text{ V}, I_{COM}$	ou – 10 mA	Room	-	4.6	5.5	
		V+ = 2.7 V, VCOM = 0.0 V / 1.0 V, ICO	JM = 101117	Full	-	-	6.5	Ω
On-resistance matching	$\Delta R_{DS(on)}$			Room	-	0.02	0.3	32
On resistance matering	DS(on)	$V+ = 2.7 \text{ V}, V_{COM} = 0.8 \text{ V} / 1.4 \text{ V}$	/ / 1.8 V,	Full	-	-	0.6	
On-resistance flatness d, f	<b>D</b>	$I_{COM} = 10 \text{ mA}$		Room	-	0.62	1.1	
On-resistance natness	R <sub>flat(on)</sub>			Full	-	-	1.5	
Off leakage current <sup>g</sup>	luo acor es			Room	-1	0.01	1	
On leakage current 9	I <sub>NC/NO(off)</sub>	$V+ = 3.6 \text{ V}, V_{NC/NO} = 1 \text{ V} / 3.$		Full	-5	-	5	
COM off leakage current <sup>g</sup>	loo: :: ::	$V_{COM} = 3.2 \text{ V} / 1 \text{ V}, V_{EN} = 0$		Room	-1	0.01	1	nA
CON On leakage current 9	I <sub>COM(off)</sub>				-5	-	5	ПД
Channel-on leakage	1	V <sub>1</sub> = 3.3 V <sub>1</sub> V <sub>2</sub> = V <sub>1</sub> = 1.1	1/221	Room	-1	0.01	1	
current <sup>g</sup>	I <sub>COM(on)</sub>	V+ = 3.5 V, V <sub>COM</sub> = V <sub>NC/NO</sub> = 1 V	$V+ = 3.3 \text{ V}, V_{COM} = V_{NC/NO} = 1 \text{ V} / 3.2 \text{ V}$		-5	-	5	
Digital Control								
Input current <sup>d</sup>	I <sub>INL</sub> or I <sub>INH</sub>			Full	-1	-	1	μΑ
Input high voltage <sup>d</sup>	$V_{INH}$			Full	1.5	-	-	\/
Input low voltage d	V <sub>INL</sub>				-	-	0.4	V
Digital input capacitance d	C <sub>IN</sub>			Room	-	3	-	pF
Dynamic Characteristics								
Town on time	1			Room	-	21	45	
Turn-on time	t <sub>ON</sub>			Full	-	-	50	- ns
T off time o		)	000.0	Room	-	11	35	
Turn-off time	t <sub>OFF</sub>	$V_{NC/NO} = 3 \text{ V}, C_L = 35 \text{ pf}, R_L =$	300 \(\Omega\)	Full	-	-	45	
Dural, hafaya washa tinas d	1			Room	3	13	-	
Break-before-make time d	t <sub>BBM</sub>			Full	2	-	-	
Charge injection <sup>d</sup>	Q <sub>INJ</sub>	C <sub>L</sub> = 1 nF, V <sub>gen</sub> = 1.5 V, R <sub>gen</sub> =	= 0 Ω	Room	-	-10.2	-	рС
Bandwidth <sup>d</sup>	BW	C <sub>L</sub> = 5 pF (set up capacitan	nce)	Room	-	222	-	MHz
Off in allation d	OIDD	D 5000 5 5 5	f = 1 MHz	Room	-	-58	-	
Off-isolation d	OIRR	$R_L = 50 \Omega$ , $C_L = 5 pF$	f = 10 MHz	Room	-	-47	-	-10
Channel to show a law at all d	X <sub>TALK</sub>	D 5000 5 5 5	f = 1 MHz	Room	-	-57	-	dB
Channel-to-channel crosstalk <sup>d</sup>		$B_1 = 50 O C_1 = 5 pF \vdash$	f = 10 MHz	Room	-	-47	-	1
NO NO Off age of the cond	C <sub>NO(off)</sub>	V+ = 2.7 V, f = 1 MHz		Room	-	7	-	İ
NO, NC Off capacitance d	C <sub>NC(off)</sub>			Room	-	7	-	1 _
0, , , ,	C <sub>NO(on)</sub>			Room	-	24	-	pF
Channel-on capacitance d	C <sub>NC(on)</sub>			Room	-	24	-	1
Power Supply	- (- /	•						
Power supply range	V+				2.7	-	3.3	V
Power supply current d	I+	V+ = 2.7 V, V <sub>IN</sub> = 0 V or 2.7	7 V	Full	-	-	1	μΑ
		v : - 2.1 v, v <sub>IIN</sub> - 0 v 01 2.1 v			1	L	1	

#### Notes

- a. Room = 25 °C, Full = as determined by the operating suffix
- b. Typical values are for design aid only, not guaranteed nor subject to production testing
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- d. Guarantee by design, not subjected to production test
- e. V<sub>IN</sub> = V+ voltage to perform proper function
- f. Crosstalk measured between channels
- g. Guarantee by 5 V testing



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SPECIFICATIONS (V+ =	= 5 V)							
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED $V+=5~V,\pm~10~\%,~V_{IN/ENL}=0.5~V,~V_{IN/ENH}=2\\V~^{\circ}$		TEMP.	LIMITS -40 °C to +85 °C			UNIT
. ,	01202			а	MIN. c	TYP. b	MAX. c	J
Analog Switch								
Analog signal ranged	$V_{ANALOG}$			Full	0	-	V+	V
Drain-source on-resistance	R <sub>DS(on)</sub>	$V_{+} = 4.5 \text{ V}, V_{COM} = 0.8 \text{ V} / 3.5 \text{ V}; I_{COM}$	. – 10 mΔ	Room	-	2.5	3.1	
Diam source on resistance	T DS(on)	V+ = 4.3 V, VCOM = 0.0 V / 3.3 V, ICOM	1 – 10 m.	Full	-	-	4	
On-resistance matching	$\Delta R_{DS(on)}$			Room	-	0.01	0.4	Ω
On resistance matering	21 (DS(on)	$V+ = 4.5 \text{ V}, V_{COM} = 0.8 \text{ V} / 2.5 \text{ V} /$	3.5 V,	Full	-	-	0.5	32
On-resistance flatness d, f	R <sub>flat(on)</sub>	$I_{COM} = 10 \text{ mA}$		Room	-	0.61	1	
	· ·iiai(on)			Full	-	-	1.5	
Off leakage current <sup>g</sup>	I <sub>NC/NO(off)</sub>			Room	-2	0.16	2	
	·NC/NO(OII)	$V+ = 5.5 \text{ V}, V_{NC/NO} = 1 \text{ V} / 4.5$		Full	-10	-	10	
COM off leakage current <sup>g</sup>	I <sub>COM(off)</sub>	$V_{COM} = 4.5 \text{ V} / 1 \text{ V}, V_{EN} = 0$	V	Room	-2	0.20	2	nA
- Com on leakage darrent	ICOM(OII)			Full	-10	-	10	100
Channel-on leakage current <sup>g</sup>	I <sub>COM(on)</sub>	$V+ = 5.5 \text{ V}, V_{COM} = V_{NC/NO} = 1 \text{ V}.$	/45V	Room	-2	0.20	2	
Chamier of realitage darrent	*COM(on)	7 00 110,110		Full	-10	-	10	
		$V+ = 0 V, V_{COM} = 5.5 V, NC/NO$	open	Full	-	0.01	5	μΑ
Power down leakage <sup>d</sup>	I <sub>PD</sub>	$V+ = 0 V$ , $V_{NC/NO} = 5.5 V$ , $COM$ , open	$V+ = 0 V$ , $V_{NC/NO} = 5.5 V$ , $COM$ , open		-	0.01	3	mA
Digital Control								
Input current d	I <sub>INL</sub> or I <sub>INH</sub>			Full	-1	-	1	μΑ
Input high voltage <sup>d</sup>	$V_{INH}$			Full	2	-	-	V
Input low voltage <sup>d</sup>	$V_{INL}$			Full	-	-	0.5	V
Digital input capacitance d	C <sub>IN</sub>				-	3	-	рF
Dynamic Characteristics								
Turn-on time	+			Room	-	14	40	
rum-on time	t <sub>ON</sub>			Full	-	-	43	
Turn-off time	+	$V_{NC/NO} = 3 \text{ V, } C_L = 35 \text{ pf, } R_L = 3$	200	Room	-	7	33	ns ns
rum-on time	t <sub>OFF</sub>	$V_{NC/NO} = 3 \text{ V, } C_L = 35 \text{ pi, } R_L = 3$	500 12	Full	-	-	35	
Break-before-make time d	+			Room	3	8	-	
Break-before-make time s	t <sub>BBM</sub>			Full	2	-	-	
Propagation delay <sup>d</sup>	tpd	$V+ = 5 V$ , no $R_L$		Room	-	325	-	ps
Charge injection <sup>d</sup>	$Q_{INJ}$	C <sub>L</sub> = 1 nF, V <sub>gen</sub> = 2.5 V, R <sub>gen</sub> =	0 Ω	Room	-	-14	-	рС
Bandwidth <sup>d</sup>	BW	C <sub>L</sub> = 5 pF (set up capacitano		Room	-	217	-	MHz
Off inclation d	OIDD	D 5000 5 75 f	= 1 MHz	Room	-	-61	-	
Off-isolation d	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	= 10 MHz	Room	-	-48	-	4D
Channel-to-channel	~	B = 50.0 C = 5.5	= 1 MHz	Room	-	-61	-	dB
crosstalk <sup>d</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ $f = 10 MHz$		Room	-	-48	-	
NO NO Off conscitance d	C <sub>NO(off)</sub>			Room	-	7	-	
NO, NC Off capacitance d	C <sub>NC(off)</sub>			Room	-	7	-	
Channel On constitute d	V+ = 5 V, I = 1 IVIHZ			Room	-	24	-	pF
Channel-On capacitance d	C <sub>NC(on)</sub>			Room	-	24	-	
Power Supply								
Power supply range	V+				4.5	_	5.5	V
Power supply current d	I+	V+ = 5.5 V, V <sub>IN</sub> = 0 V or 5.5 V		Full	-	-	1	μΑ
		/ 114			•		-	

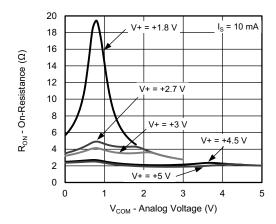
### Notes

- a. Room = 25 °C, Full = as determined by the operating suffix
- b. Typical values are for design aid only, not guaranteed nor subject to production testing
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- d. Guarantee by design, not subjected to production test
- e. V<sub>IN</sub> = input voltage to perform proper function
- f. Difference of min and max values
- g. Guaranteed by 5 V testing.

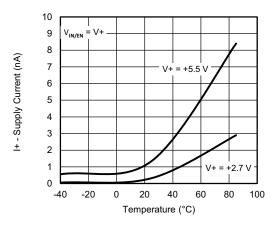
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



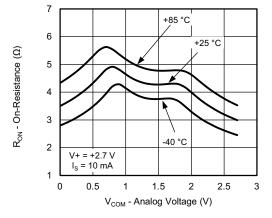
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



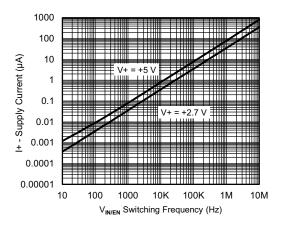
R<sub>ON</sub> vs. V<sub>COM</sub> and Single Supply Voltage



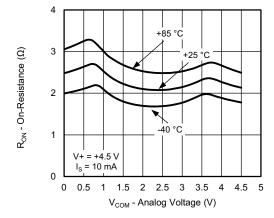
**Supply Current vs. Temperature** 



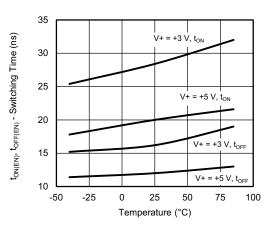
R<sub>ON</sub> vs. Analog Voltage and Temperature



Positive Supply Current vs. Switching Frequency



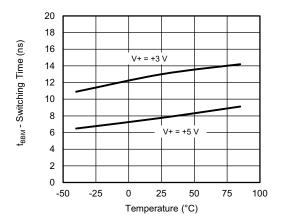
R<sub>ON</sub> vs. Analog Voltage and Temperature



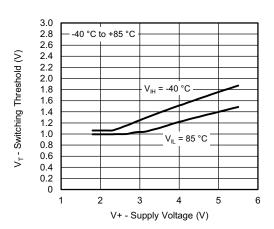
Switching Time vs. Temperature



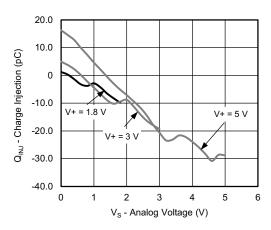
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



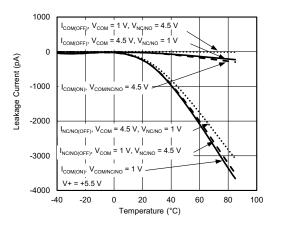
Switching Time vs. Temperature



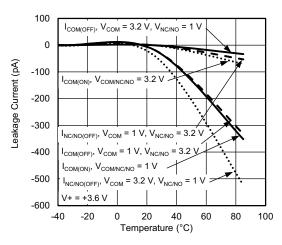
Switching Threshold vs. Supply Voltage



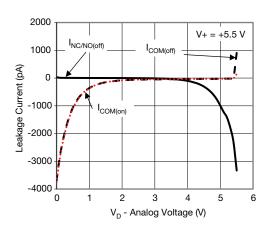
Charge Injection vs. Source Voltage



Leakage Current vs. Temperature



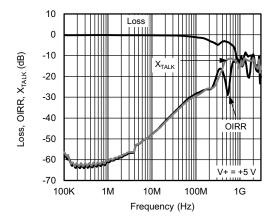
Leakage Current vs. Temperature



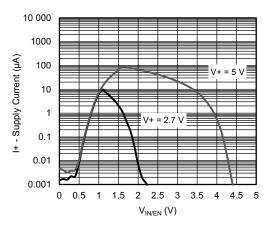
Leakage Current vs. Analog Voltage



### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

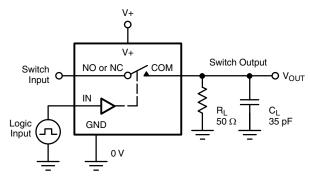


Loss, OIRR, X<sub>TALK</sub> vs. Frequency



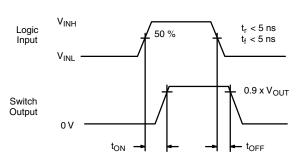
Positive Supply Current vs. Logic Voltage

### **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

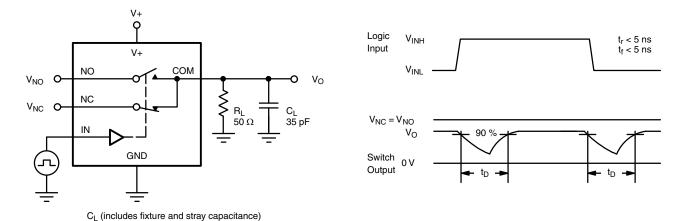
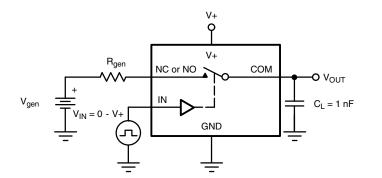
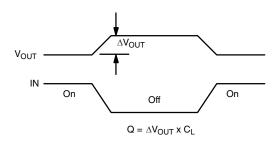


Fig. 2 - Break-Before-Make Interval

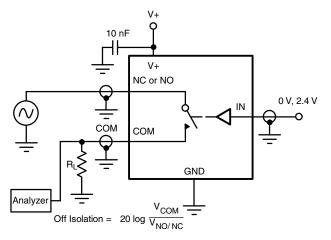
### **TEST CIRCUITS**





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 3 - Charge Injection



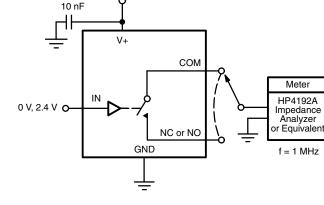


Fig. 4 - Off-Isolation

Fig. 5 - Channel Off/On Capacitance

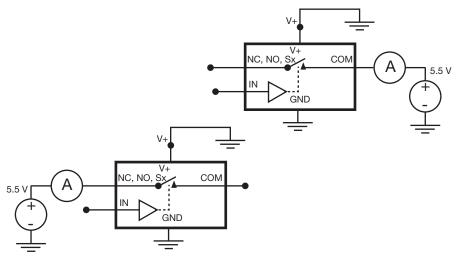


Fig. 6 - Source / Drain Power Down Leakage

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg278595">www.vishay.com/ppg278595</a>.

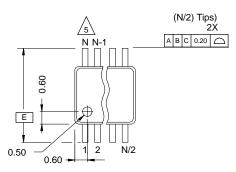




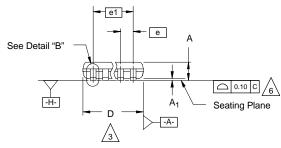


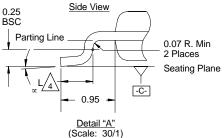
#### MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)



Top View







Die thickness allowable is  $0.203 \pm 0.0127$ .



Dimensions "D" and "E<sub>1</sub>" do not include mold flash or protrusions, and are measured at Datum plane [-H-], mold flash or protrusions shall not exceed 0.15 mm per side.

Dimension is the length of terminal for soldering to a substrate.

Terminal positions are shown for reference only.

Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.

The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".

Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

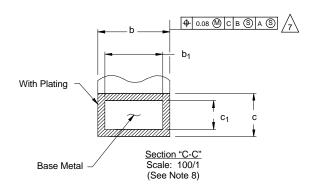
Controlling dimension: millimeters.

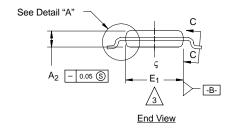
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

Datums -A- and -B- to be determined Datum plane -H-.

Exposed pad area in bottom side is the same as teh leadframe pad size.







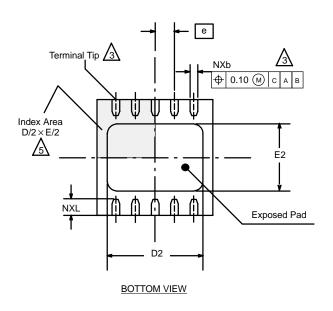
N = 10L

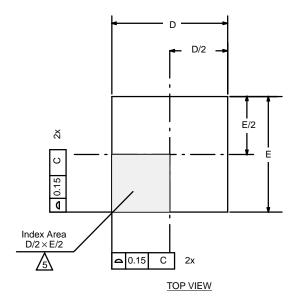
n l			
	Nom	Max	Note
	-	1.10	
5	0.10 0.15		
5	0.85	0.95	
7	-	0.27	8
7	0.20	0.23	8
3	-	0.23	
3	0.15	0.18	
3.00 BSC			
4.	90 BSC		
)	3.00	3.10	3
0.	50 BSC	•	
2.	00 BSC		
)	0.55	0.70	4
10		5	
	4°	6°	
		10	10 4° 6°

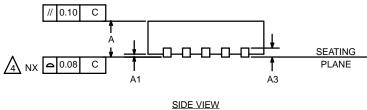
Document Number: 71245



### **DFN-10 LEAD (3 X 3)**







### NOTES:

1. All dimensions are in millimeters and inches.

N is the total number of terminals.

Dimension b applies to metallized terminal and is measured between 0.15 and 0.30 mm from terminal tip.  $\,$ 



Coplanarity applies to the exposed heat sink slug as well as the



The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.

	MI	LLIMETE	RS	INCHES				
Dim	Min	Nom	Max	Min	Nom	Max		
Α	0.80	0.90	1.00	0.031	0.035	0.039		
A1	0.00	0.02	0.05	0.000	0.001	0.002		
А3		0.20 BSC		0.008 BSC				
b	0.18	0.23	0.30	0.007 0.009 0.012				
D		3.00 BSC			0.118 BSC			
D2	2.20	2.38	2.48	0.087 0.094 0.09				
Е		3.00 BSC		0.118 BSC				
E2	1.49	1.64	1.74	0.059	0.065	0.069		
е		0.50 BSC		0.020 BSC				
L	0.30	0.40	0.50	0.012	0.016	0.020		
*Use millimeters as the primary measurement.								
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